

## Innovating Energy Technology

http://www.fujielectric.com/products/semiconductor/ Discrete IGBT

## Discrete IGBT (High-Speed XS-series) 650V / 75A

#### Features

Low power loss Low switching surge and noise High reliability, high ruggedness (RBSOA, SCSOA etc.)

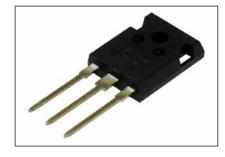
#### Applications

Uninterruptible power supply PV Power coditionner Inverter welding machine

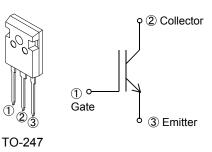
#### Maximum Ratings and Characteristics

● Absolute Maximum Ratings at T<sub>vi</sub> = 25 °C (unless otherwise specified)

Parameter	Symbol	Value	Unit	Remarks
Collector-Emitter Voltage	VCES	650	V	
Gate-Emitter Voltage	VGES	± 20	v	
Transient Gate-Emitter Voltage	VGES	± 30	v	t₀ < 1 µs
DC Collector Current	Ic@25	115	Α	<i>T</i> <sub>c</sub> = 25 °C
	Ic@100	75	Α	<i>T</i> <sub>c</sub> = 100 °C
Pulsed Collector Current	I <sub>CP</sub>	300	Α	Note *1
Turn-Off Safe Operating Area	-	300	А	V <sub>CE</sub> ≤ 650 V T <sub>vj</sub> ≤ 175 °C
Max. Power Dissipation	Ptot	437	W	Tc = 25 °C
<b>Operating Junction Temperature</b>	Tvj	-40 ~ +175	°C	
Storage Temperature	T <sub>stg</sub>	-55 ~ +175	°C	



#### Equivalent circuit



Note \*1 : Pulse width limited by T<sub>vj max</sub>.

#### ● Electrical Characteristics at *T*<sub>vi</sub> = 25 °C (unless otherwise specified)

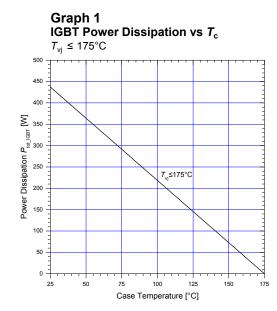
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Zero Gate Voltage	, ,	$V_{\rm CE} = 650 \text{ V}$ $T_{\rm vj} = 25 \text{ °C}$	-	-	250	μA
Collector Current	ICES	$V_{GE} = 0 V$ $T_{vj} = 175 ^{\circ}C$	-	-	2	mA
Gate-Emitter	,	V <sub>CE</sub> = 0 V			200	nA
Leakage Current	IGES	$V_{\text{GE}} = \pm 20 \text{ V}$	-	-	200	ΠA
Gate-Emitter	V <sub>GE(th)</sub>	V <sub>CE</sub> = 20 V	3.4	4.0	4.6	V
Threshold Voltage	V GE(th)	<i>I</i> c = 75 mA				v
Collector-Emitter		$V_{GE} = 15 \text{ V}$ $\frac{T_{vj} = 25 \text{ °C}}{7}$	1.0	1.35	1.7	
Saturation Voltage	V <sub>CE(sat)</sub>	$V_{GE} = 15 \text{ V}$ $I_{C} = 75 \text{ A}$ $T_{vj} = 125 \text{ °C}$	-	1.5	-	V
Saturation voltage		$T_{\rm vj} = 175 ^{\circ}{\rm C}$	-	1.6	-	
Input Capacitance	Cies	V <sub>CE</sub> = 25 V	2970	5940	8910	
Output Capacitance	$C_{\text{oes}}$ $V_{\text{GE}} = 0 \text{ V}$		67	134	201	pF
Reverse Transfer Capacitance	Cres	f = 1 MHz	30	60	90	
· · · · · · · · · · · · · · · · · · ·		V <sub>cc</sub> = 520 V				
Gate Charge	QG	/c = 75 A	150	300	450	nC
		V <sub>GE</sub> = 15 V				
Turn-On Delay Time	t <sub>d(on)</sub>	<i>T</i> <sub>vi</sub> = 25 °C	22	44	66	
Rise Time	tr	$V_{cc} = 400 V$	29	58	87	ns
Turn-Off Delay Time	t <sub>d(off)</sub>	/c = 37.5 A	170	340	510	115
Fall Time	tr	V <sub>GE</sub> = 15 V 14		28	42	
Turn-On Energy	Eon	$R_{\rm G} = 10 \ \Omega$		1.3	1.95	- m l
Turn-Off Energy	Eoff	Energy loss include "tail" and FWD reverse recovery.	0.47	0.94	1.35 mJ	
Turn-On Delay Time	t <sub>d(on)</sub>	<i>T</i> <sub>vi</sub> = 150 °C	22	44	66	
Rise Time	tr	$V_{cc} = 400 V$	27	54	81	
Turn-Off Delay Time	t <sub>d(off)</sub>	Ic = 37.5 A	190	380	570	ns
Fall Time	ti	V <sub>GE</sub> = 15 V	23	46	69	1
Turn-On Energy	Eon	$R_{\rm G} = 10 \Omega$	0.8	1.6	2.4	
Turn-Off Energy	Eoff	Energy loss include "tail" and FWD reverse recovery.	0.5	1	1.5	mJ

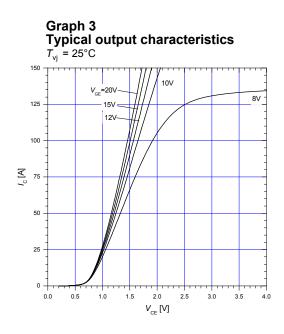
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#### Thermal Resistance

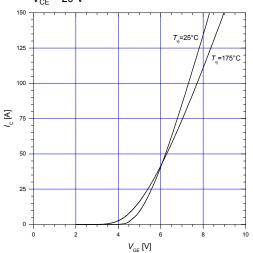
Parameter	Symbol	Min.	Тур.	Max.	Unit
Thermal Resistance, Junction-Ambient	R <sub>th(j-a)</sub>	-	-	50	°C/W
Thermal Resistance, Junction to Case	R <sub>th(j-c)</sub>	-	-	0.343	°C/W

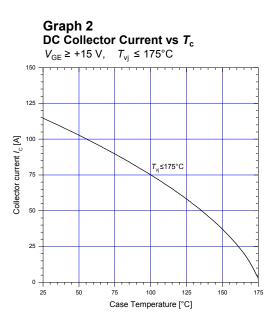
### Characteristics (Representative)



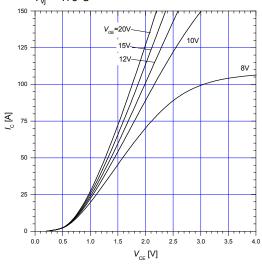


Graph 5 Typical transfer characteristics V<sub>CE</sub> = 20 V

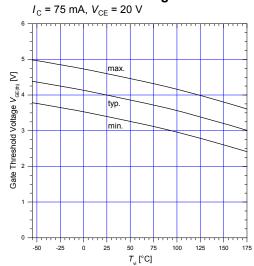


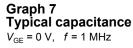




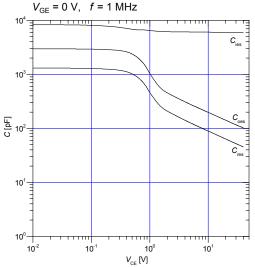


Graph 6 Gate threshold voltage

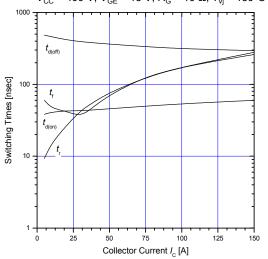




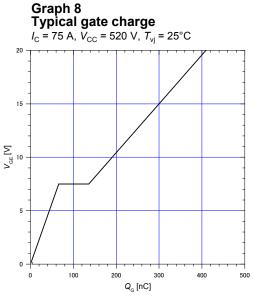
Graph 9



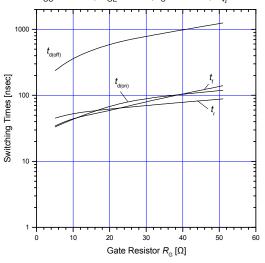
0 0 100 Graph 10 Typical switching times vs. Ic  $V_{\rm CC} = 400 \text{ V}, V_{\rm GE} = 15 \text{ V}, R_{\rm G} = 10 \Omega, T_{\rm vj} = 150^{\circ}\text{C}$ 

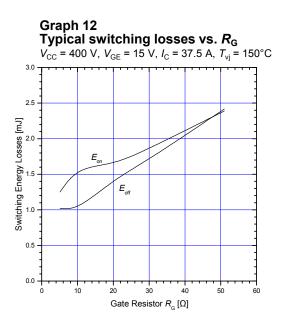


Graph 11 Typical switching losses vs. Ic  $V_{\rm CC} = 400 \text{ V}, V_{\rm GE} = 15 \text{ V}, R_{\rm G} = 10 \Omega, T_{\rm vi} = 150^{\circ}\text{C}$ 20 Switching Energy Losses [mJ] E  $E_{\rm off}$ 0 75 25 50 100 125 0 150 Collector Current I<sub>c</sub> [A]

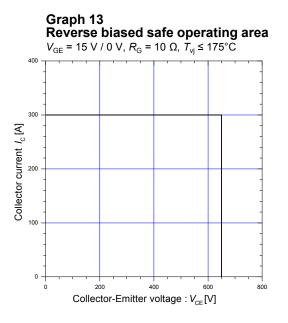


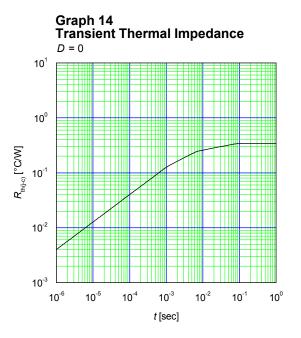
Typical switching times vs. R<sub>G</sub>  $V_{\rm CC} = 400 \text{ V}, V_{\rm GE} = 15 \text{ V}, I_{\rm C} = 37.5 \text{ A}, T_{\rm vi} = 150^{\circ}\text{C}$ 





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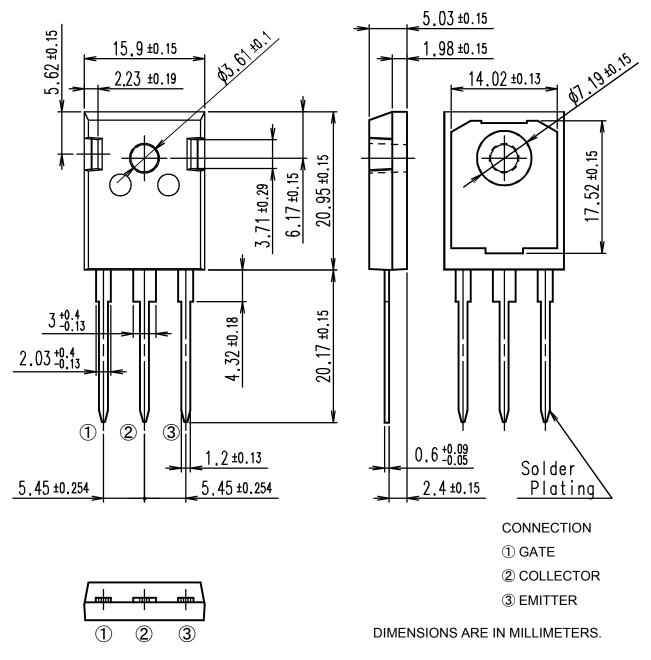




## FGW75XS65

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## Outline Drawings, mm



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<ul> <li>Traffic-signal con</li> <li>Emergency equip</li> <li>Medical equipme</li> </ul>	ment for responding to disas	sters and anti-burglary devices		rs with an auto-shut-off feature
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